

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number: F475R12KS4B11BOSA1

Manufacturer: Infineon Technologies

Package: Module

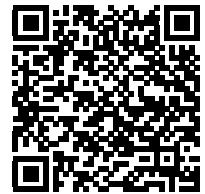
Availability: Please confirm with sales

Product Page:

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Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

Preliminary datasheet

EconoPACK™2 module with the fast IGBT2 for high-frequency switching and PressFIT / NTC

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{ nom}} = 75\text{ A} / I_{CRM} = 150\text{ A}$
 - High short-circuit capability
 - Low switching losses
- Mechanical features
 - Isolated base plate
 - Copper base plate
 - PressFIT contact technology
 - RoHS compliant
 - Standard housing



Typical appearance

Potential applications

- Inductive heating and welding
- UPS systems

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

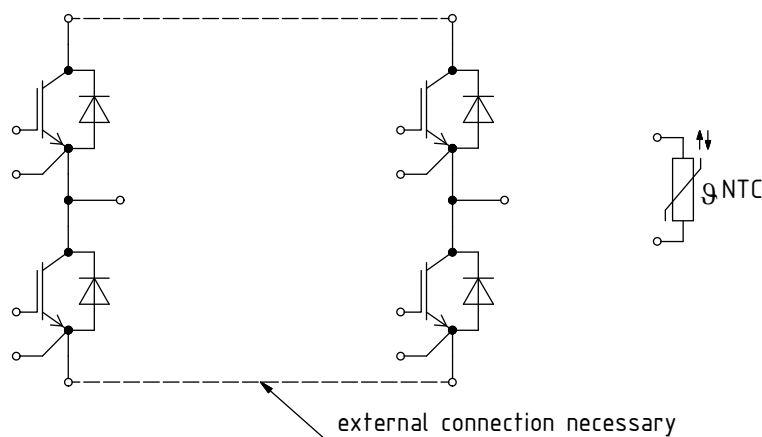


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to heatsink	7.5	mm
Comparative tracking index	CTI		> 200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			30		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25^\circ\text{C}$, per switch		2.2		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	3		6	Nm
Weight	G			180		g

Note: The current under continuous operation is limited to 50 A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		$T_{vj} = 25^\circ\text{C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 150^\circ\text{C}$	$T_C = 65^\circ\text{C}$	75	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj \text{ op}}$		150	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 75\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		3.20	3.75	V
			$T_{vj} = 125\ ^\circ C$		3.85		
Gate threshold voltage	V_{GETh}	$I_C = 3\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		4.5	5.5	6.5	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V$			0.8		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			5		Ω
Input capacitance	C_{ies}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			5.1		nF
Reverse transfer capacitance	C_{res}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.3		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			1	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 75\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 7.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.120		μs
			$T_{vj} = 125\ ^\circ C$		0.130		
Rise time (inductive load)	t_r	$I_C = 75\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 7.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.050		μs
			$T_{vj} = 125\ ^\circ C$		0.060		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 75\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 7.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.310		μs
			$T_{vj} = 125\ ^\circ C$		0.360		
Fall time (inductive load)	t_f	$I_C = 75\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 7.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.020		μs
			$T_{vj} = 125\ ^\circ C$		0.030		
Turn-on energy loss per pulse	E_{on}	$I_C = 75\ A, V_{CC} = 600\ V, L_\sigma = 30\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 7.5\ \Omega, di/dt = 2000\ A/\mu s (T_{vj} = 125\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		5		mJ
			$T_{vj} = 125\ ^\circ C$		9		
Turn-off energy loss per pulse	E_{off}	$I_C = 75\ A, V_{CC} = 600\ V, L_\sigma = 30\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 7.5\ \Omega, dv/dt = 7000\ V/\mu s (T_{vj} = 125\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		2.6		mJ
			$T_{vj} = 125\ ^\circ C$		3.8		
SC data	I_{SC}	$V_{GE} \leq 15\ V, V_{CC} = 900\ V, V_{CEmax} = V_{CES} - L_{SCE} * di/dt$	$t_p \leq 10\ \mu s, T_{vj} = 125\ ^\circ C$		450		A
Thermal resistance, junction to case	R_{thJC}	per IGBT				0.250	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1\ W/(m \cdot K)$			0.120		K/W
Temperature under switching conditions	$T_{vj\ op}$			-40		125	$^\circ C$

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25\text{ °C}$	1200	V
Continuous DC forward current	I_F			75	A
Repetitive peak forward current	I_{FRM}	$t_P = 1\text{ ms}$		150	A
I^2t - value	I^2t	$t_P = 10\text{ ms}$, $V_R = 0\text{ V}$	$T_{vj} = 125\text{ °C}$	2450	A ² s

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 75\text{ A}$, $V_{GE} = 0\text{ V}$		$T_{vj} = 25\text{ °C}$	2.00	V
				$T_{vj} = 125\text{ °C}$	1.70	
Peak reverse recovery current	I_{RM}	$V_{CC} = 600\text{ V}$, $I_F = 75\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 2000\text{ A}/\mu\text{s}$ ($T_{vj} = 125\text{ °C}$)		$T_{vj} = 25\text{ °C}$	43	A
				$T_{vj} = 125\text{ °C}$	62	
Recovered charge	Q_r	$V_{CC} = 600\text{ V}$, $I_F = 75\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 2000\text{ A}/\mu\text{s}$ ($T_{vj} = 125\text{ °C}$)		$T_{vj} = 25\text{ °C}$	4.5	μC
				$T_{vj} = 125\text{ °C}$	13	
Reverse recovery energy	E_{rec}	$V_{CC} = 600\text{ V}$, $I_F = 75\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 2000\text{ A}/\mu\text{s}$ ($T_{vj} = 125\text{ °C}$)		$T_{vj} = 25\text{ °C}$	1.7	mJ
				$T_{vj} = 125\text{ °C}$	4.7	
Thermal resistance, junction to case	R_{thJC}	per diode			0.550	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		0.260		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		125	°C

4 NTC-Thermistor

Table 7 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25\text{ °C}$		5		kΩ
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100\text{ °C}$, $R_{100} = 493\text{ }\Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25\text{ °C}$			20	mW

(table continues...)

Table 7 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		3433		K

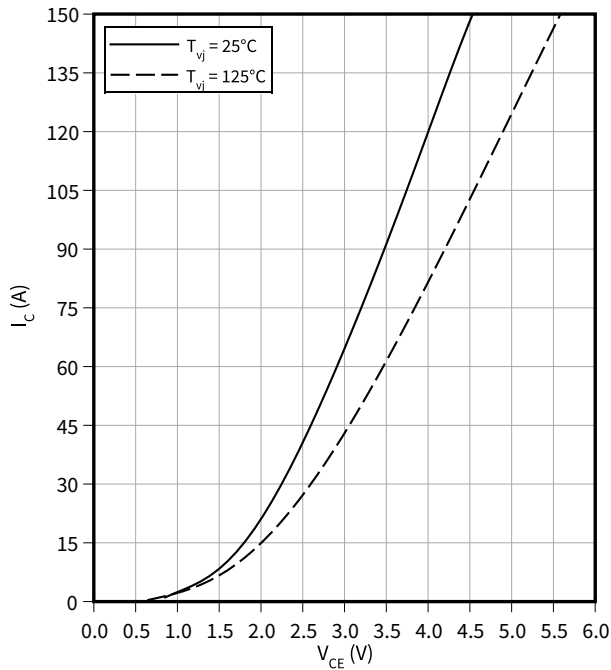
Note: Specification according to the valid application note.

5 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

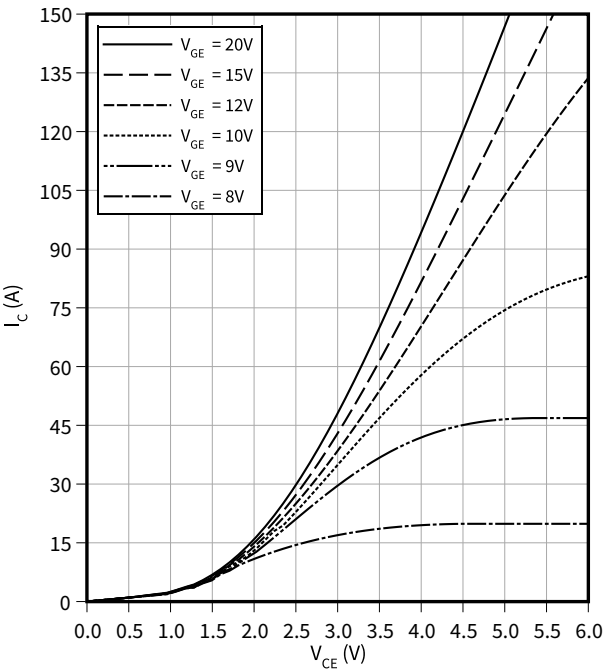
$V_{GE} = 15\text{ V}$



Output characteristic field (typical), IGBT, Inverter

$I_C = f(V_{CE})$

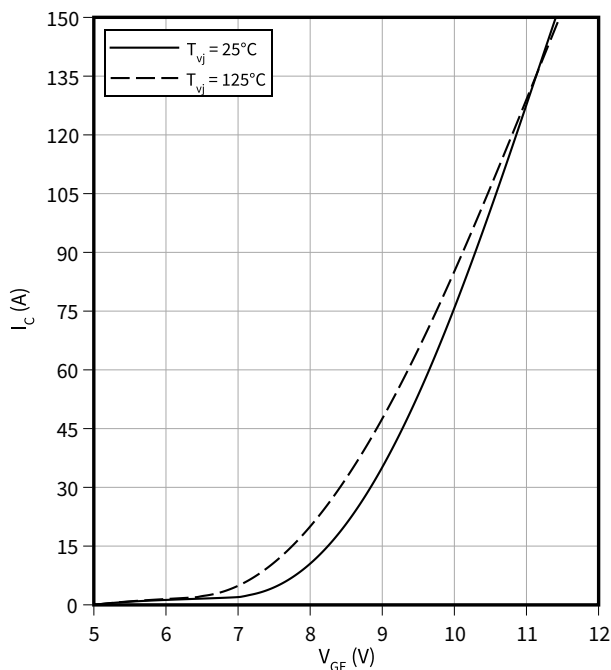
$T_{vj} = 125\text{ °C}$



Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

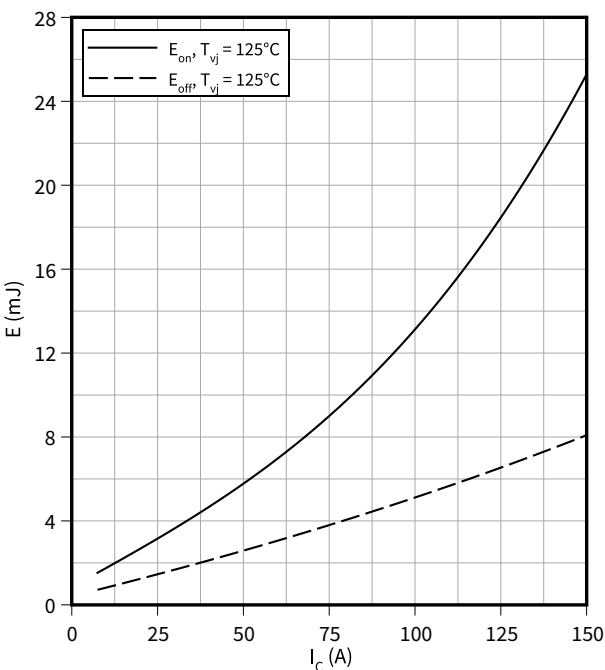
$V_{CE} = 20\text{ V}$



Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

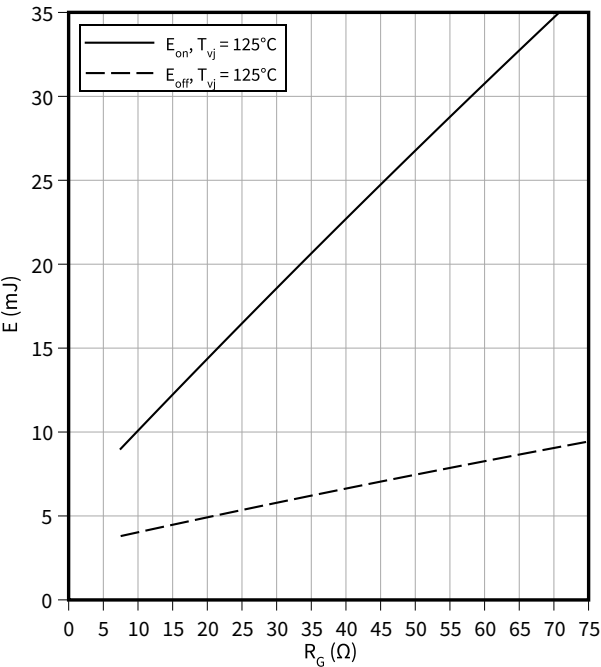
$R_{Goff} = 7.5\text{ }\Omega$, $R_{Gon} = 7.5\text{ }\Omega$, $V_{GE} = \pm 15\text{ V}$, $V_{CC} = 600\text{ V}$



5 Characteristics diagrams

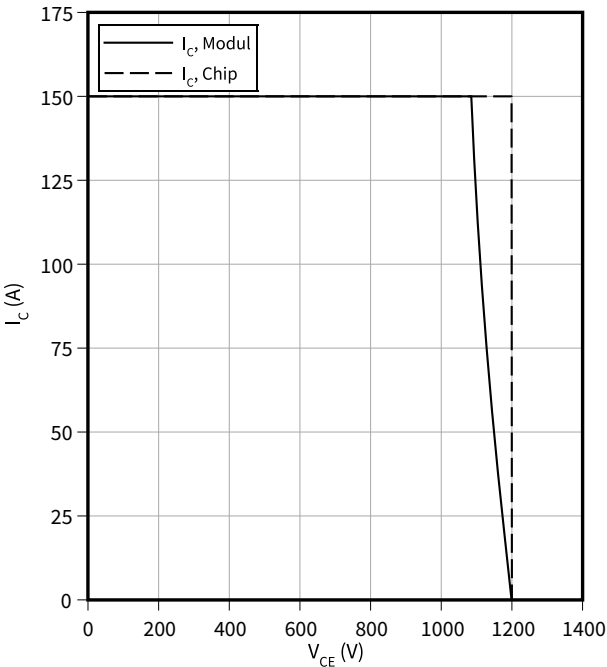
Switching losses (typical), IGBT, Inverter

$E = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 75\text{ A}$, $V_{CC} = 600\text{ V}$



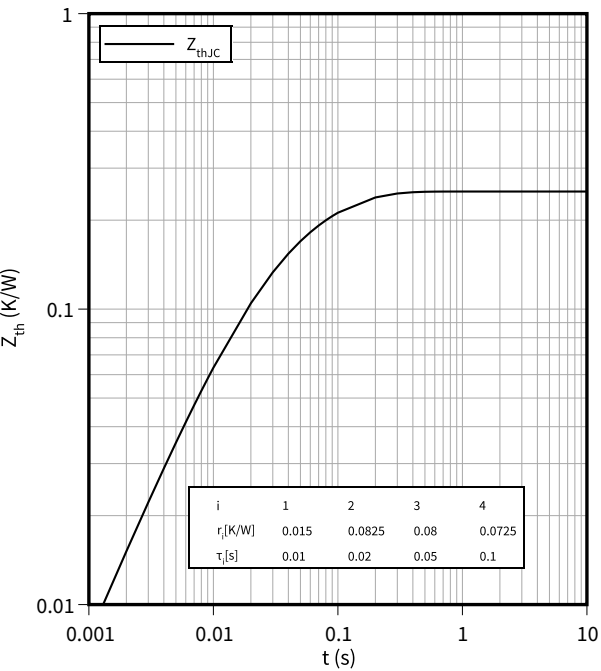
Reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$
 $R_{Goff} = 7.5\text{ }\Omega$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 125\text{ }^\circ\text{C}$



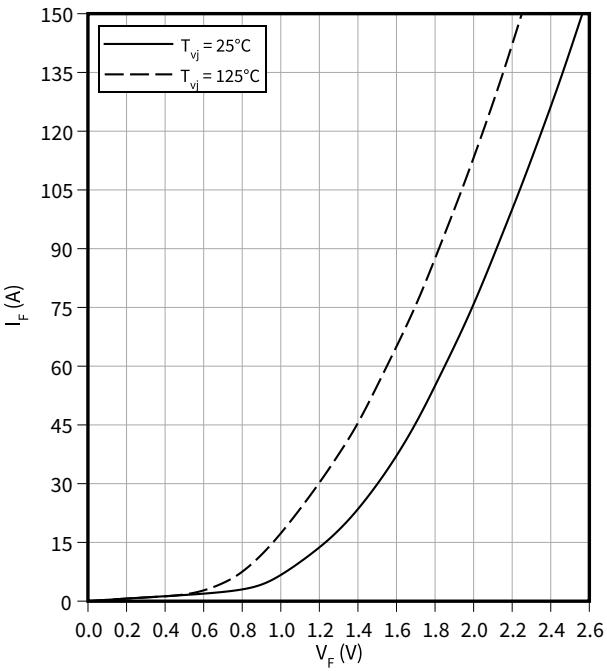
Transient thermal impedance, IGBT, Inverter

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, Inverter

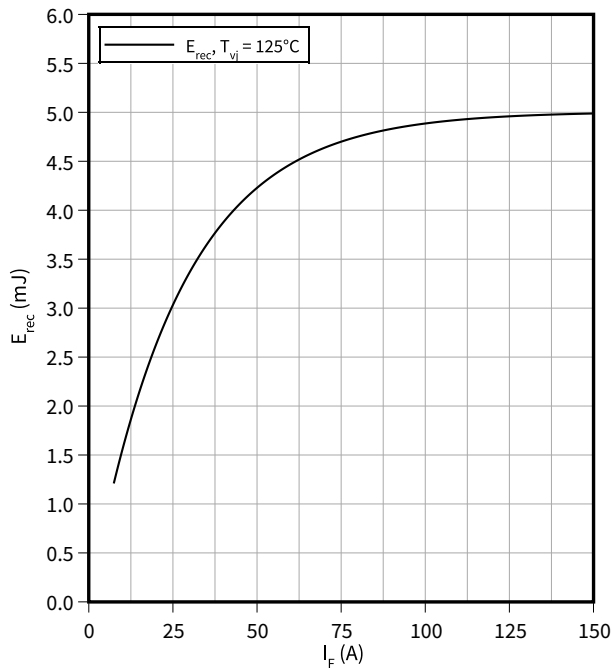
$I_F = f(V_F)$



5 Characteristics diagrams

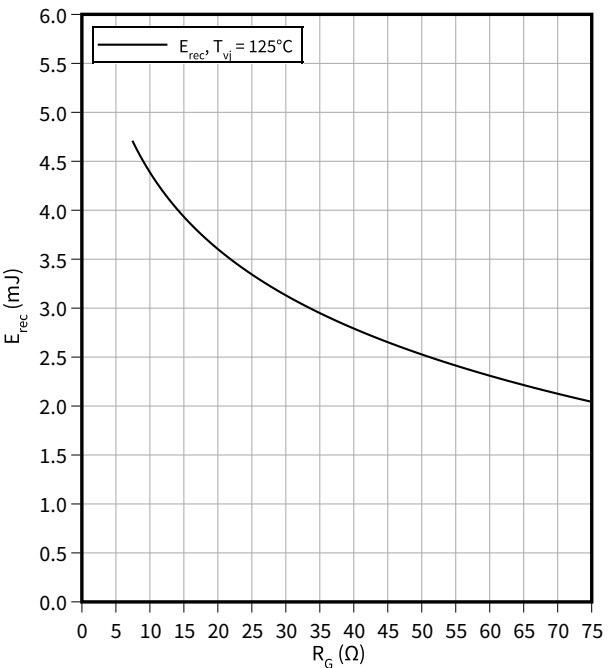
Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$
 $R_{Gon} = 7.5 \, \Omega, V_{CC} = 600 \, V$



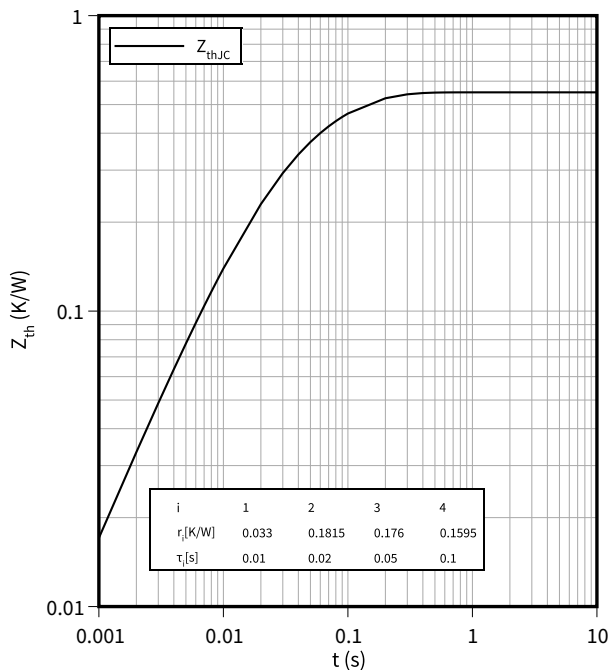
Switching losses (typical), Diode, Inverter

$E_{rec} = f(R_G)$
 $I_F = 75 \, A, V_{CC} = 600 \, V$



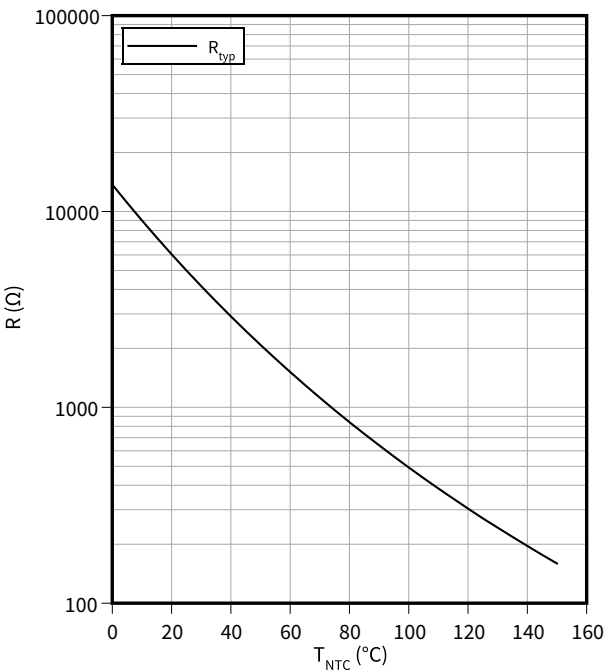
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



6 Circuit diagram

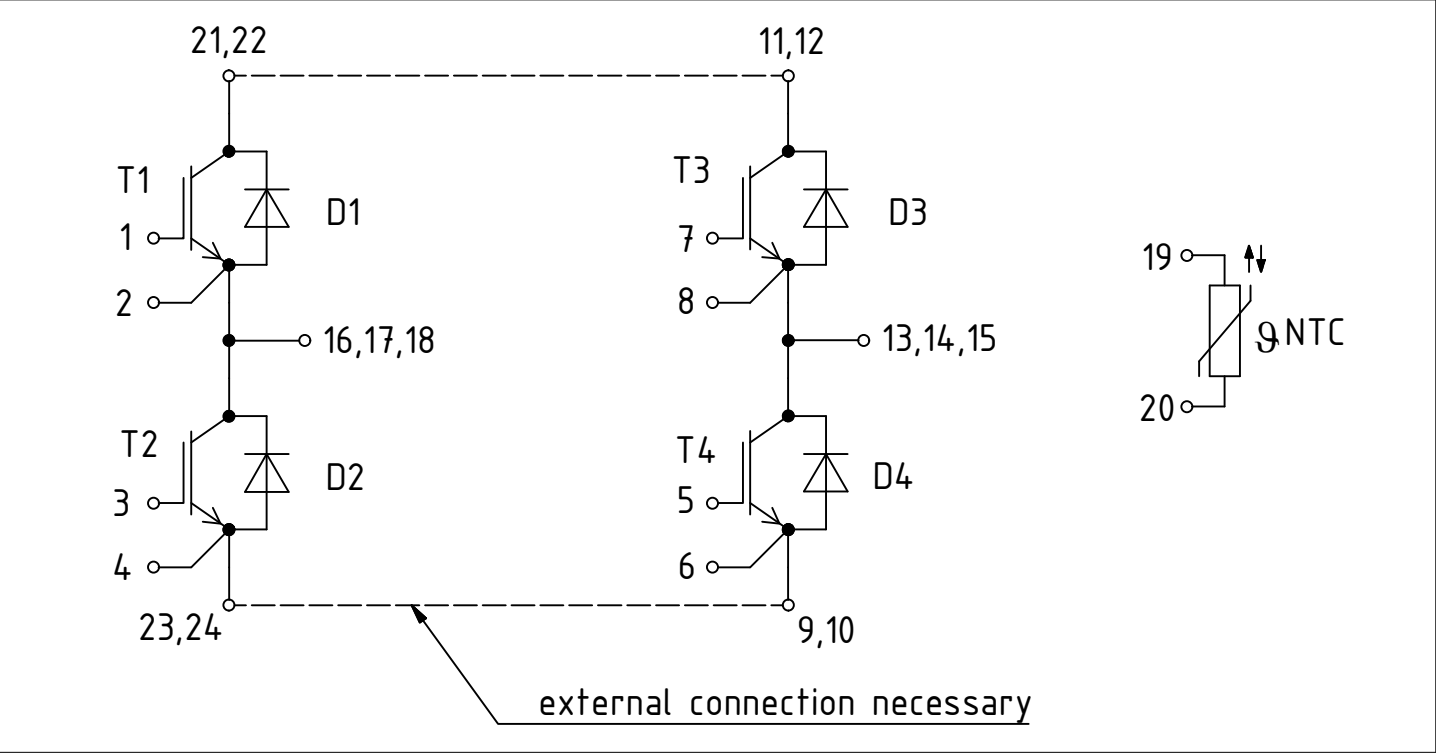


Figure 1



Revision 0.20
2024-01-25

8 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	Content	Digit	Example
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30
Example	 7154914284655054991153071549142846550549911530		

Figure 3



Revision history

Revision history

Document revision	Date of release	Description of changes
V1.0	2011-07-19	Target datasheet
V2.0	2011-10-18	Preliminary datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
0.20	2024-01-25	Preliminary datasheet

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